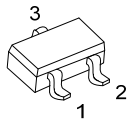
UK3019

Power MOSFET

2.5V DRIVE SILICON N-CHANNEL MOSFET



SOT-23-3
(JEDEC TO-236)

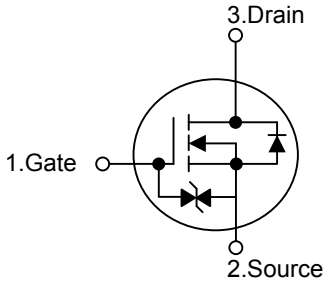
■ DESCRIPTION

The UTC **UK3019** is a silicon N-channel MOSFET which has been designed to minimize on-state resistance while it provides rugged, reliable and fast switching performance. The product is particularly suited for low voltage, low current applications such as small servo motor controller, power MOSFET gate drivers, and other switching applications.

■ FEATURES

* Min V_{DSS} =30V
* $R_{DS(ON)}$ ≤ 8.0Ω @ I_D=10mA, V_{GS}=4.0V
* $R_{DS(ON)}$ ≤ 13Ω @ I_D=1mA, V_{GS}=2.5V
* Pulsed ID=400mA
* Low Voltage Drive (2.5V)

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UK3019L-AE2-R	UK3019G-AE2-R	SOT-23-3	G	S	D	Tape Reel

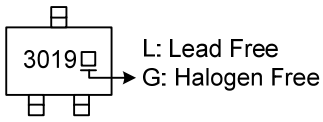
Note: Pin Assignment: G: Gate S: Source D: Drain

UK3019G-AE2-R

(1)Packing Type
(2)Package Type
(3)Green Package

(1) R: Tape Reel
(2) AE2: SOT-23-3
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	100	mA
	Pulsed (Note 2)	I_{DP}	400	mA
Power Dissipation (Note 3)		P_D	200	mW
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Pw≤10μs, Duty cycle≤50%
3. With each pin mounted on the recommended lands.

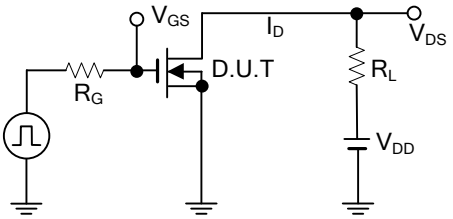
■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	625	°C/W

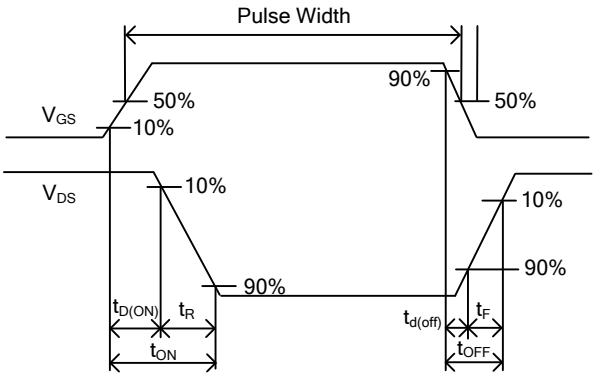
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=10μA	30			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=3V,I_D=100μA	0.8		1.5	V
Static drain-source on-state resistance	$R_{DS(ON)}$	I_D=10mA, V_{GS}=4.0V		5.0	8.0	Ω
		I_D=1mA, V_{GS}=2.5V		7.0	13	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS}=5V, V_{GS}=0V, f = 1MHz		13		pF
Output Capacitance	C_{OSS}			9		pF
Reverse Transfer Capacitance	C_{RSS}			4		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	V_{GS}=5V, V_{DD}≈5V I_D=10mA, R_L=500Ω, R_G=10Ω		15		ns
Turn-ON Rise Time	t_R			35		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			80		ns
Turn-OFF Fall-Time	t_F			80		ns

■ TEST CIRCUITS AND WAVEFORMS



Switching Time Measurement Circuit



Switching Time Waveforms